

ABSTRACT OF THE DISCLOSURE

A surface emitting semiconductor laser includes: a semiconductor substrate; a first semiconductor multilayer reflection film of a first conduction type on the semiconductor  
5 substrate; a second semiconductor multilayer reflection film of a second conduction type; an active region and a current confining layer interposed between the first and second semiconductor multilayer reflection films; and a  
10 low-resistance layer interposed between the current confining layer and the active region.